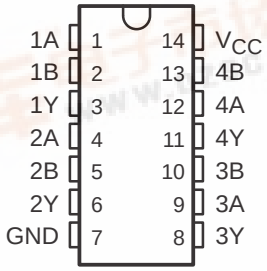
SN54ACT00, SN74ACT00
QUADRUPLE 2-INPUT POSITIVE-NAND GATES

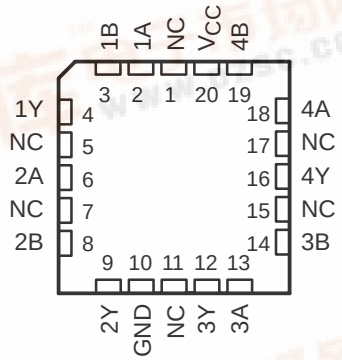
SCAS523B – AUGUST 1995 – REVISED AUGUST 1999

- **Inputs Are TTL-Voltage Compatible**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) 1-μm Process**
- **Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), DIP (N) Packages, Ceramic Chip Carriers (FK), Flat (W), and DIP (J) Packages**

SN54ACT00 . . . J OR W PACKAGE
SN74ACT00 . . . D, DB, N, OR PW PACKAGE
(TOP VIEW)



SN54ACT00 . . . FK PACKAGE
(TOP VIEW)



NC – No internal connection

description

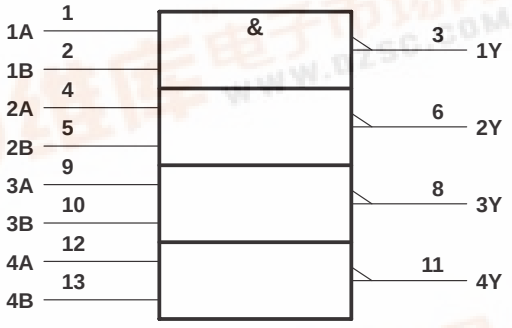
The ‘ACT00 devices contain four independent 2-input NAND gates. Each gate performs the Boolean function of $Y = \overline{A \bullet B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

The SN54ACT00 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ACT00 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE
(each gate)

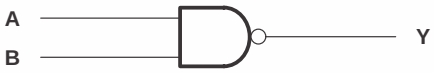
INPUTS		OUTPUT
A	B	Y
H	H	L
L	X	H
X	L	H

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.
Pin numbers shown are for the D, DB, J, N, PW, and W packages.

logic diagram, each gate (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 7 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Note 1) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0 or V_I > V_{CC}) . . . . . ±20 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±20 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±200 mA
Package thermal impedance, θ_{JA} (see Note 2): D package . . . . . 127°C/W
DB package . . . . . 158°C/W
N package . . . . . 78°C/W
PW package . . . . . 170°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.

recommended operating conditions (see Note 3)

		SN54ACT00		SN74ACT00		UNIT
		MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage	4.5	5.5	4.5	5.5	V
V_{IH}	High-level input voltage	2		2		V
V_{IL}	Low-level input voltage		0.8		0.8	V
V_I	Input voltage	0	V_{CC}	0	V_{CC}	V
V_O	Output voltage	0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current		– 24		– 24	mA
I_{OL}	Low-level output current		24		24	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	0	8	0	8	ns/V
T_A	Operating free-air temperature	–55	125	–40	85	°C

NOTE 3: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	T_A = 25°C			SN54ACT00		SN74ACT00		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V_{OH}	I_{OH} = – 50 µA	4.5 V	4.4	4.49		4.4		4.4		V
		5.5 V	5.4	5.49		5.4		5.4		
	I_{OH} = – 24 mA	4.5 V	3.86			3.7		3.76		
		5.5 V	4.86			4.7		4.76		
	I_{OH} = – 50 mA†	5.5 V				3.85				
	I_{OH} = – 75 mA†	5.5 V						3.85		
V_{OL}	I_{OL} = 50 µA	4.5 V		0.001	0.1		0.1		0.1	V
		5.5 V		0.001	0.1		0.1		0.1	
	I_{OL} = 24 mA	4.5 V			0.36		0.5		0.44	
		5.5 V			0.36		0.5		0.44	
	I_{OL} = 50 mA†	5.5 V					1.65			
	I_{OL} = 75 mA†	5.5 V							1.65	
I_I	$V_I = V_{CC}$ or GND	5.5 V			±0.1		±1		±1	µA
I_{CC}	$V_I = V_{CC}$ or GND, I_O = 0	5.5 V			2		40		20	µA
ΔI_{CC}‡	One input at 3.4 V, Other inputs at GND or V_{CC}	5.5 V		0.6			1.6		1.5	mA
C_i	$V_I = V_{CC}$ or GND	5 V		2.6						pF

† Not more than one output should be tested at a time, and the duration of the test should not exceed 2 ms.
‡ This is the increase in supply current for each input that is at one of the specified TTL voltage levels rather than 0 V or V_{CC}.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see Figure 1)

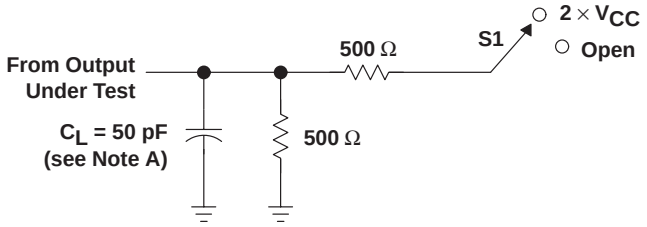
PARAMETER	FROM (INPUT)	TO (OUTPUT)	T_A = 25°C			SN54ACT00		SN74ACT00		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A or B	Y	1.5	5.5	9	1	9.5	1	9.5	ns
t_{PHL}			1.5	4	7	1	8	1	8	

operating characteristics, V_{CC} = 5 V, T_A = 25°C

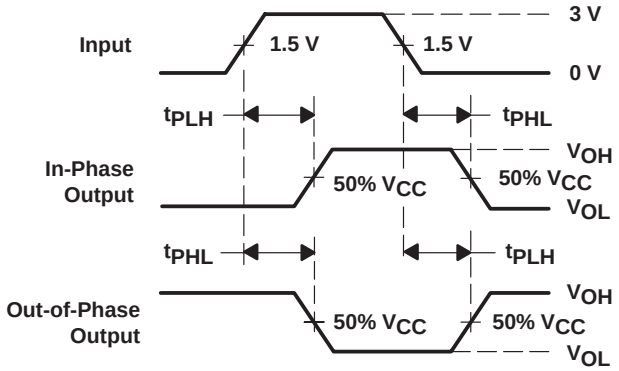
PARAMETER		TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF, f = 1 MHz	40	pF

PARAMETER MEASUREMENT INFORMATION

TEST	S1
t_{PLH}/t_{PHL}	Open



LOAD CIRCUIT



VOLTAGE WAVEFORMS

NOTES: A. C_L includes probe and jig capacitance.
B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
C. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

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